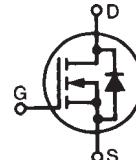


PolarHT™ HiPerFET Power MOSFET

IXFH 69N30P
IXFT 69N30P

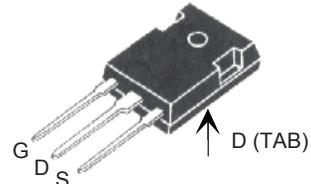
V_{DSS}	=	300	V
I_{D25}	=	69	A
$R_{DS(on)}$	\leq	49	$m\Omega$
t_{rr}	\leq	200	ns

N-Channel Enhancement Mode
Fast Intrinsic Diode
Avalanche Rated

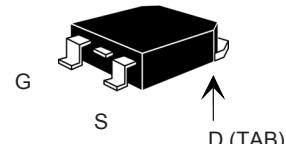


Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	300	V	
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$; $R_{GS} = 1 M\Omega$	300	V	
V_{GS}	Continuous	± 20	V	
V_{GSM}	Transient	± 30	V	
I_{D25}	$T_c = 25^\circ C$	69	A	
I_{DM}	$T_c = 25^\circ C$, pulse width limited by T_{JM}	200	A	
I_{AR}	$T_c = 25^\circ C$	69	A	
E_{AR}	$T_c = 25^\circ C$	50	mJ	
E_{AS}	$T_c = 25^\circ C$	1.5	J	
dv/dt	$I_s \leq I_{DM}$, $di/dt \leq 100 A/\mu s$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$, $R_G = 4 \Omega$	10	V/ns	
P_D	$T_c = 25^\circ C$	500	W	
T_J		-55 ... +150	$^\circ C$	
T_{JM}		150	$^\circ C$	
T_{stg}		-55 ... +150	$^\circ C$	
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ C$	
T_{SOLD}	Plastic body for 10 s	260	$^\circ C$	
M_d	Mounting torque	1.13/10	Nm/lb.in.	
Weight	TO-247 TO-268	6 4	g g	

TO-247 (IXFH)



TO-268 (IXFT)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 V$, $I_D = 250 \mu A$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 mA$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20 V_{DC}$, $V_{DS} = 0$		± 100	nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$		25 250	μA
$R_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu s$, duty cycle d $\leq 2 \%$		49	$m\Omega$

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic diode

Advantages

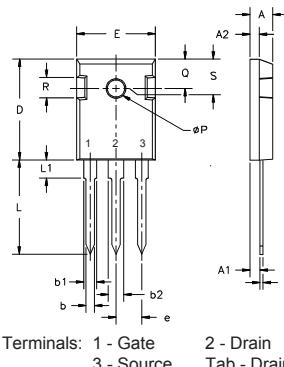
- Easy to mount
- Space savings
- High power density

Symbol **Test Conditions**
Characteristic Values
 $(T_J = 25^\circ C, \text{ unless otherwise specified})$

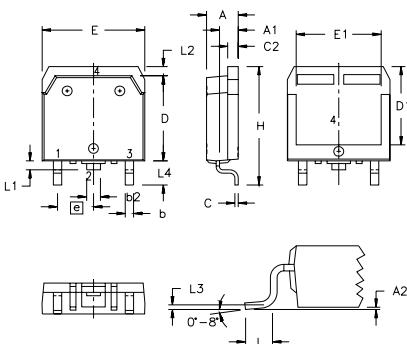
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10 V; I_D = 0.5 I_{D25}$, pulse test	30	48	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 V, V_{DS} = 25 V, f = 1 \text{ MHz}$	4960	pF	
		760	pF	
		190	pF	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = I_{D25}$ $R_G = 4 \Omega$ (External)	25	ns	
		25	ns	
		75	ns	
		27	ns	
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$	156	180	nC
		32	nC	
		79	nC	
R_{thJC}	(TO-247)		0.25	°C/W
R_{thCS}		0.21		°C/W

Source-Drain Diode
Characteristic Values
 $(T_J = 25^\circ C, \text{ unless otherwise specified})$

		Min.	Typ.	Max.
I_s	$V_{GS} = 0 V$			69 A
I_{SM}	Repetitive			200 A
V_{SD}	$I_F = I_S, V_{GS} = 0 V$, Pulse test, $t \leq 300 \mu s$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25 A$	100	200	ns
	$-di/dt = 100 A/\mu s$		500	nC
Q_{RM}	$V_R = 100 V, V_{GS} = 0 V$			

TO-247 AD Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

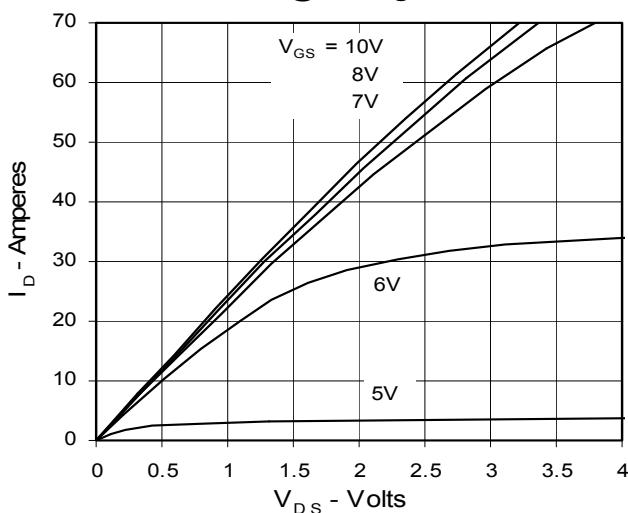
TO-268
Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

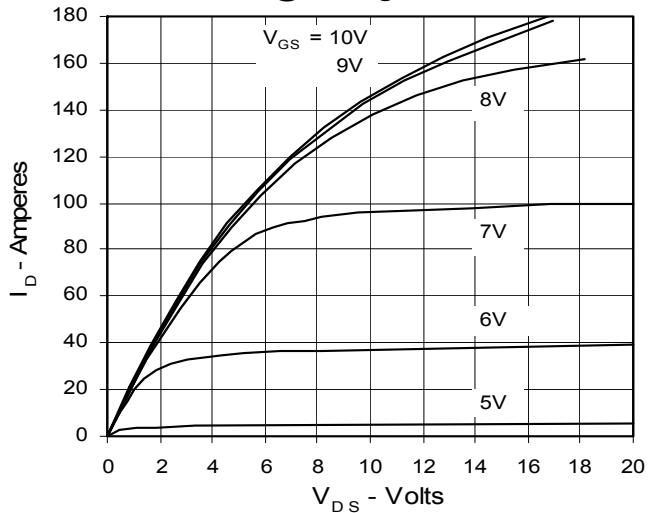
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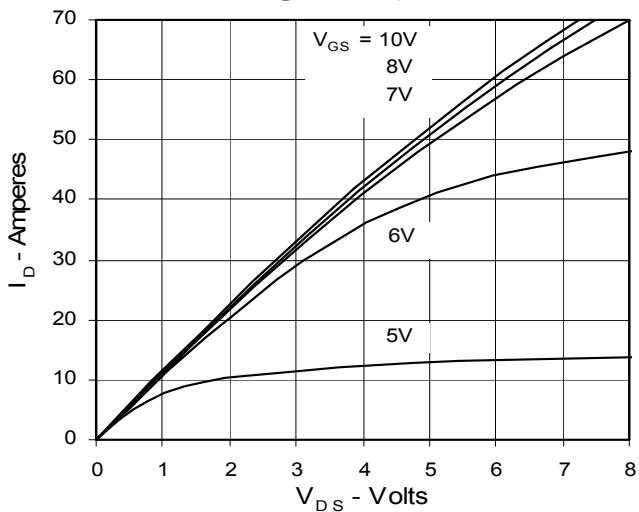
**Fig. 1. Output Characteristics
@ 25 Deg. C**



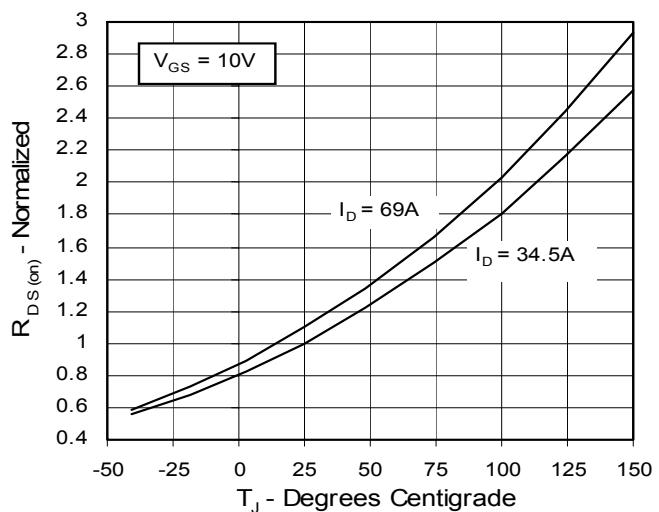
**Fig. 2. Extended Output Characteristics
@ 25 deg. C**



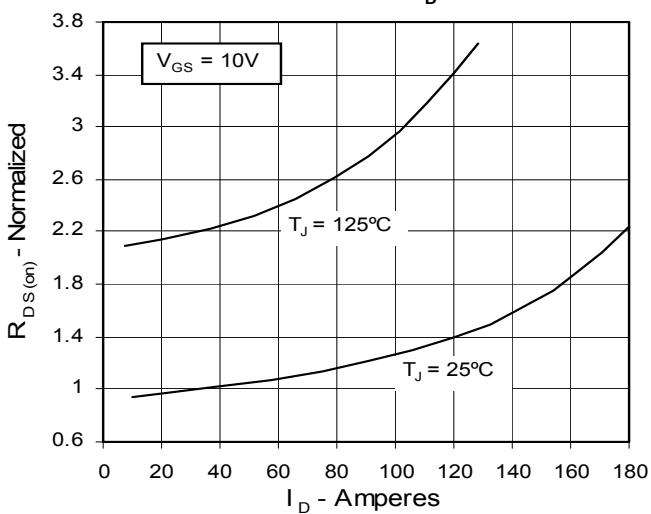
**Fig. 3. Output Characteristics
@ 125 Deg. C**



**Fig. 4. $R_{DS(on)}$ Normalized to I_{D25} Value vs.
Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to I_{D25}
Value vs. I_D**



**Fig. 6. Drain Current vs. Case
Temperature**

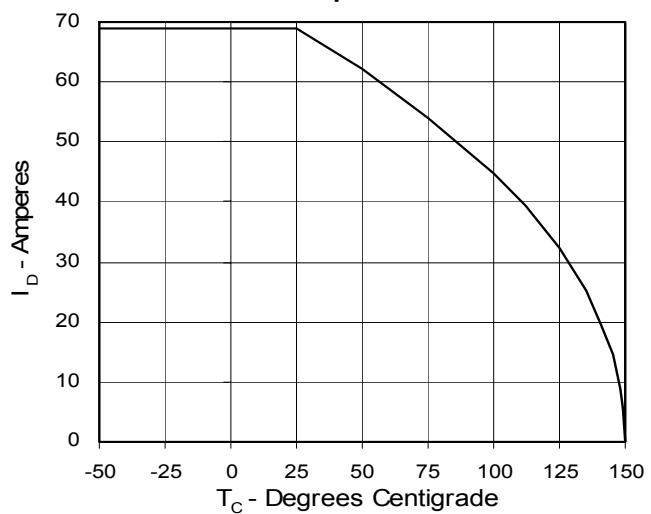


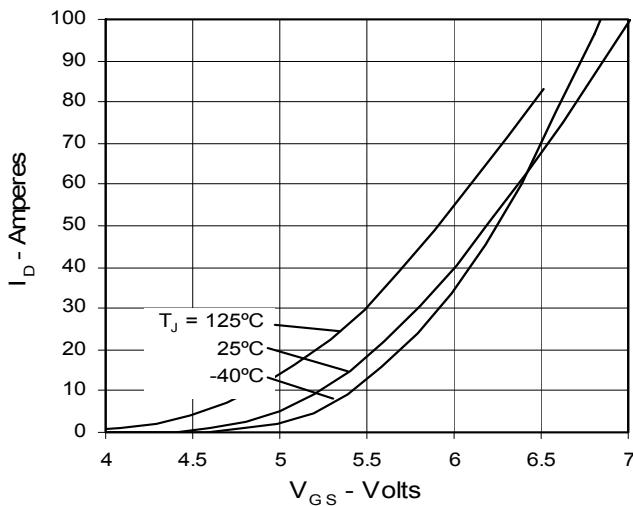
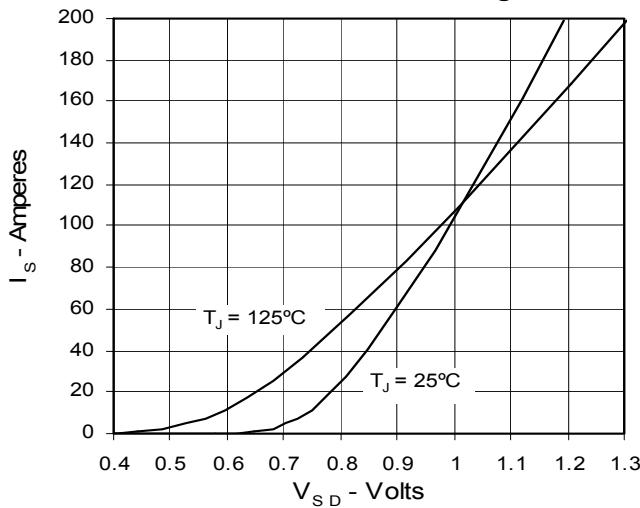
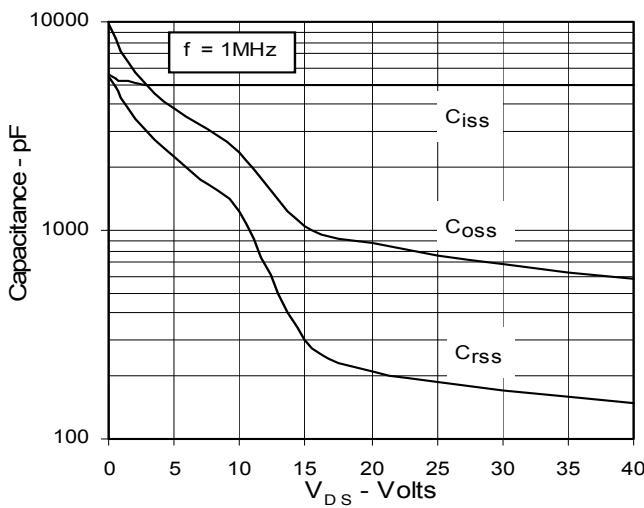
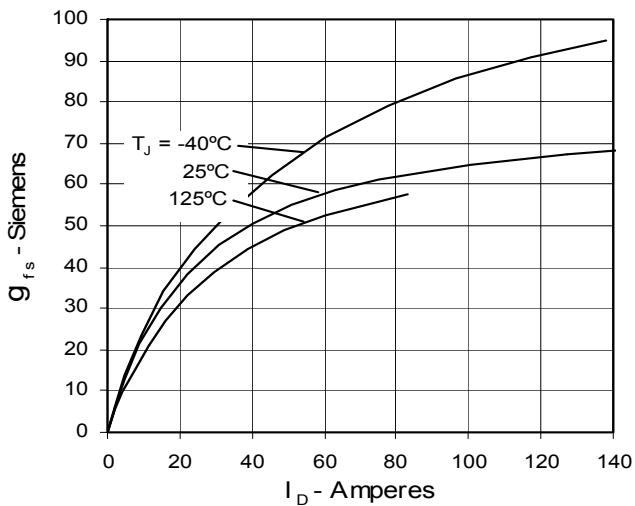
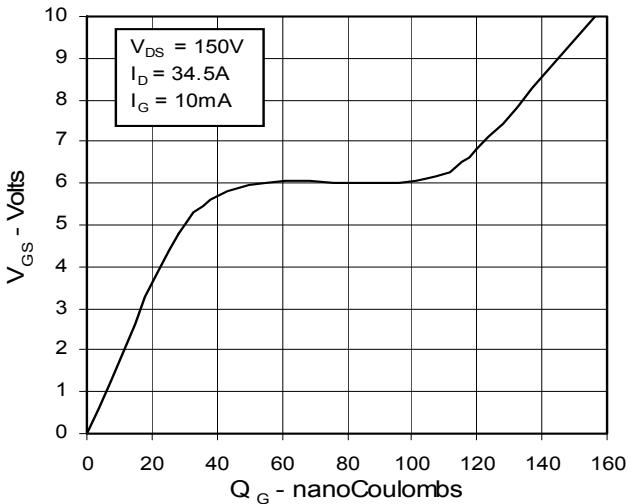
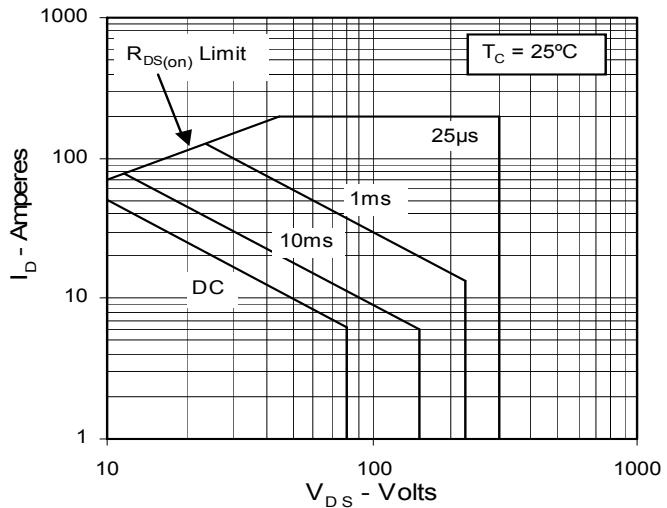
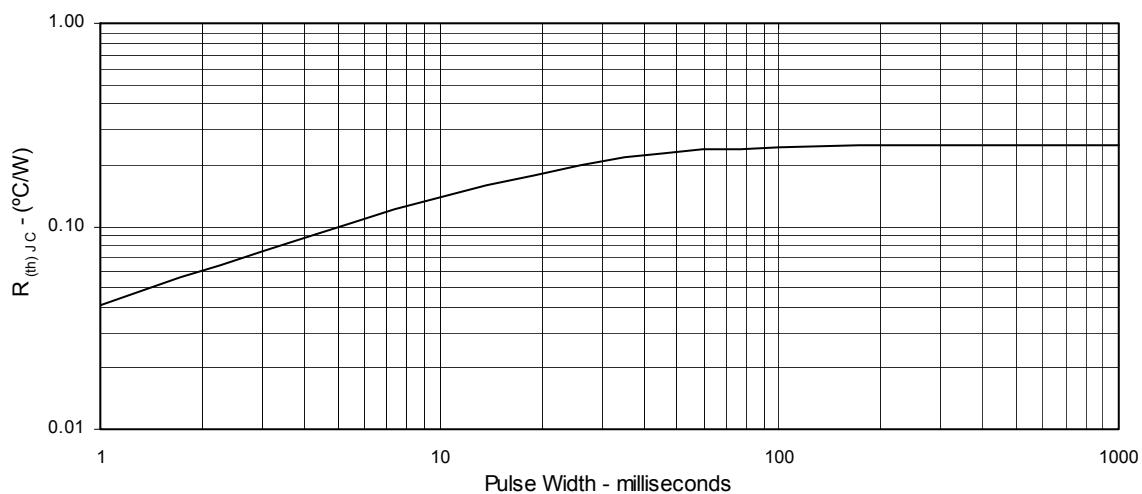
Fig. 7. Input Admittance

Fig. 9. Source Current vs. Source-To-Drain Voltage

Fig. 11. Capacitance

Fig. 8. Transconductance

Fig. 10. Gate Charge

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Maximum Transient Thermal Resistance



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